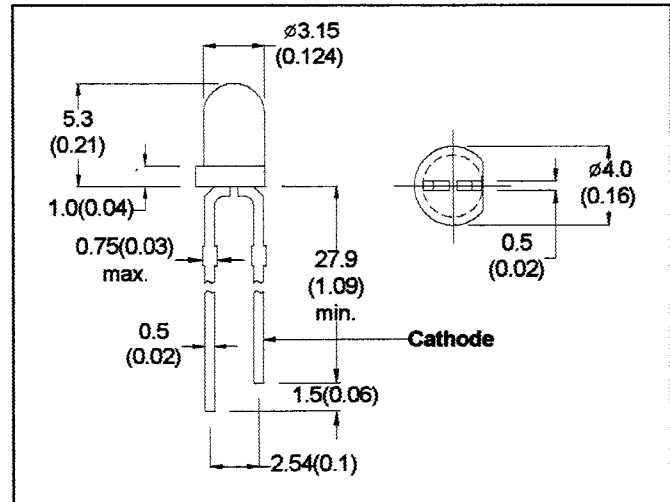


MICRO ELECTRONICS

INFRARED EMITTING DIODE

DESCRIPTION

MIB31T is GaAlAs infrared emitting diode molded in T-1 standard 3mm diameter clear transparent lens.



- All Dimension in mm (inch)
- NO Scale
- Tol : +/- 0.3mm

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	5V
Power Dissipation	200mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	P _o	1.6	2.5		mW	I _F =20mA
Forward Voltage	V _F		1.2	1.6	V	I _F =20mA
Reverse Current	I _R			100	μA	V _R =5V
Peak Wavelength	λ _p		940		nm	I _F =20mA
Spectrum Line Half Width	Δλ		45		nm	I _F =20mA
Viewing Angle	2θ 1/2		40		degree	I _F =20mA

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